

Aluminum-Induced Crystallization (AIC) of Nano-crystalline silicon thin films deposited by Plasma Enhanced Chemical Vapor Deposition (PECVD)

Abstract

The process of Aluminum-Induced Crystallization (AIC) has given an advantage of transforming the a-Si to pc-Si, which is very attractive due to the significant improvement of film characteristics, relatively easy to process, allow a variety of substrates like plastic and glass due to the low process temperature.

The characterization of the film we have deposited using Plasma Enhanced Chemical Vapor Deposition (PECVD), have shown the film has already some poly-crystalline percentage/grains, that will help study the AIC in new way not only within this work, but also in the future plans.